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### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Ki-Yeon Park, et al.

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Serial No.

10/713,577

Examiner:

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Filed:

November 12, 2003

Art Unit:

2818

For:

CAPACITOR OF SEMICONDUCTOR MEMORY DEVICE THAT HAS COMPOSITE Al<sub>2</sub>O<sub>3</sub>/HfO<sub>2</sub> DIELECTRIC LAYER AND METHOD OF MANUFACTURING THE SAME

## INFORMATION DISCLOSURE CITATION FORM PTO-1449 (Modified)

#### **U.S. PATENT DOCUMENTS**

Exam | Ref

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Class

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PV \_

2002/0115252

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Haukka et al.

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#### **FOREIGN PATENT DOCUMENTS**

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Name

Dr.

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### **OTHER DOCUMENTS**

Exam

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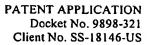
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SAME

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M	<del></del>	P2002-0034520	May 9, 2002	Korea	
		OTHER DOCUMENTS			
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